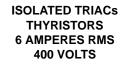
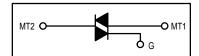
Triacs Silicon Bidirectional Triode Thyristors

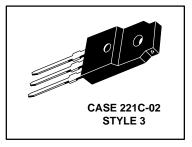
... designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 400 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Isolated Construction for Low Thermal Resistance, High Heat Dissipation and Durability









Rating	Symbol	Value	Unit	
Repetitive Peak Off-State Voltage(1) (T _J = -40 to +100°C, Gate Open)	VDRM	400	Volts	
On-State RMS Current ($T_C = +80^{\circ}C$) ⁽²⁾ (Full Cycle Sine Wave 50 to 60 Hz)	IT(RMS)	6	Amps	
Peak Non–repetitive Surge Current (One Full Cycle, 60 Hz, T _C = +80°C)	ITSM	60	Amps	
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	40	A ² s	
Peak Gate Power (T _C = +80°C, Pulse Width = 1 μ s)	P _{GM}	1	Watt	
Average Gate Power ($T_C = +80^{\circ}C$, t = 8.3 ms)	P _{G(AV)}	0.2	Watt	
Peak Gate Trigger Current (Pulse Width = 10 μs)	IGTM	4	Amps	
RMS Isolation Voltage (T _A = 25°C, Relative Humidity \leq 20%)	VISO	1500	Volts	
Operating Junction Temperature Range	TJ	-40 to +100	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case ⁽²⁾	R _θ JC	2.7	°C/W
Case to Sink	R _θ CS	2.2(typ)	
Junction to Ambient	R _θ JA	60	

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.



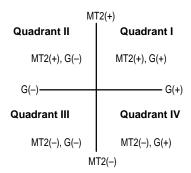
T2500DFP

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Off–State Current (Either Direction) $(V_D = Rated V_{DRM}, T_J = 100^{\circ}C, Gate Open)$	IDRM	—	—	2	mA
Maximum On-State Voltage (Either Direction)* (I _T = 30 A Peak)	VTM	-	—	2	Volts
Gate Trigger Current (Continuous dc) (V _D = 12 Vdc, R _L = 12 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	IGT		10 20 15 30	25 60 25 60	mA
Gate Trigger Voltage (Continuous dc) (All Quadrants) ($V_D = 12 Vdc, R_L = 12 Ohms$) ($V_D = V_{DROM}, R_L = 125 Ohms, T_C = 100^{\circ}C$, All Trigger Models)	VGT	 0.2	1.25 —	2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 150 mA, $T_C = 25^{\circ}C$)	Ч	-	15	30	mA
Gate Controlled Turn-On Time $(V_D = Rated V_{DRM}, I_T = 10 A, I_{GT} = 160 mA, Rise Time \leq 0.1 \ \mu s)$	tgt	-	1.6	_	μs
Critical Rate–of–Rise of Commutation Voltage (V_D = Rated V_{DRM} , $I_T(RMS)$ = 6 A, Commutating di/dt = 3.2 A/ms, Gate Unenergized, T_C = 80°C)	dv/dt(c)	-	10	—	V/µs
Critical Rate–of–Rise of Off–State Voltage (V_D = Rated V_{DRM} , Exponential Voltage Rise, Gate Open, T _C = 100°C)	dv/dt	-	100	_	V/µs

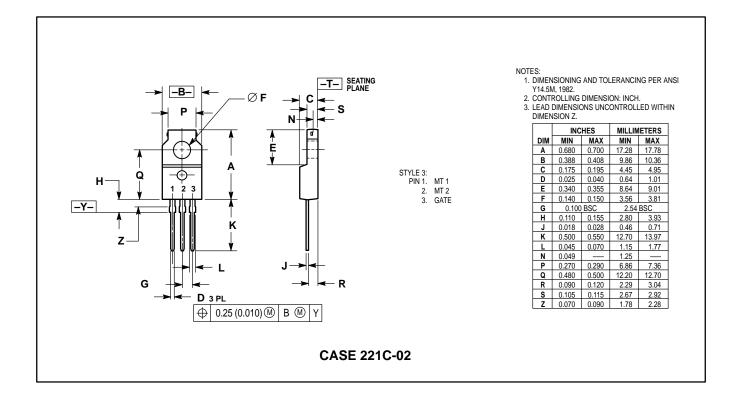
*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

Quadrant Definitions



T2500DFP

PACKAGE DIMENSIONS



T2500DFP

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How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 1–303–675–2140 or 1–800–441–2447

Customer Focus Center: 1-800-521-6274

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ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Centre, 2, Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong. 852–26629298

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan. 81-3-5487-8488

JAPAN: Motorola Japan Ltd.; SPD, Strategic Planning Office, 141,

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